

ABSTRACT

5 An object of the present invention is to provide a
method of producing a Group III nitride semiconductor
device having a chip form which is pentagonal or more
highly polygonal maintaining good area efficiency and at
a low cost.

10 The inventive method of producing a Group III
nitride semiconductor device having a chip shape which is
a pentagonal or more highly polygonal shape comprises a
first step of epitaxially growing a Group III nitride
semiconductor on a substrate to form a semiconductor
wafer; a second step of irradiating said semiconductor
wafer with a laser beam to form separation grooves; a
15 third step of grinding and/or polishing the main surface
side differently from the epitaxially grown main surface
of the substrate; and a fourth step of division into
individual chips by applying stress to said separation
grooves.